TOSHIBA CDMOS Integrated Circuit Silicon Monolithic

T C 6 2 D 9 0 2 F G

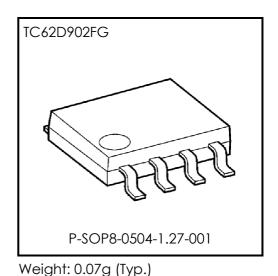
Offline Isolated flyback LED Controller with PFC

1. Feature

This product is isolated fly back LED controller IC with the power factor correction function.

A LED current that flows to the secondary-side of transformer is controlled by feedback primary-side of transformer. Therefore, the Photo coupler is not used. External parts can be decreased compared with a past isolated fly back system.

Moreover, PFC function of one converter type is built into, and the power factor improvement is possible by few parts.



2. Use of recommend

LED lighting

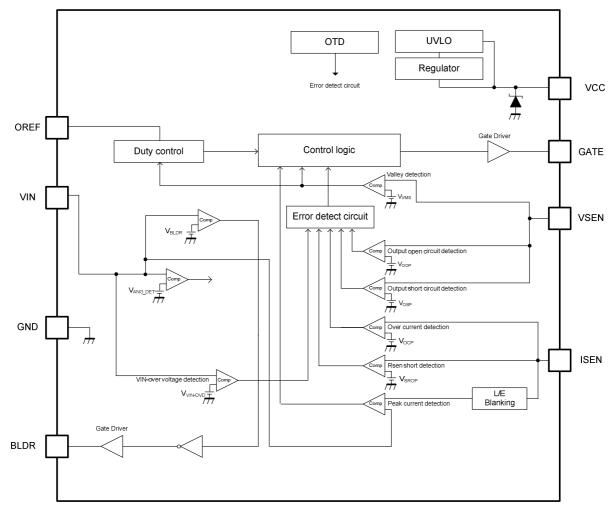
3. Characteristics

- Isolated PFC LED driver with minimum number of external parts
- TRIAC Dimmable
- 1 converter type PFC (PFC >0.9)
- Opto-isolator not need (Few parts and High Reliability)
- Valley switch operation (Efficiency improvement & EMI reduction)
- Detection function

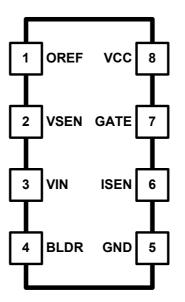
Under voltage lockout (UVLO) VIN over voltage detection (VIN-OVD) Sense resistor short detection (SRSD) Sense line open detection (IOD) Over temperature detection (OTD) Output open circuit detection (OOD) Output short circuit detection (OSD) Over current detection (OCD)

• Package: P-SOP8-0504-1.27-001

4. Block Diagram



5. Pin Assignment (top view)



6. Pin Functions

Pin No	Pin Name	I/O	Function
1	OREF	I	Capacitor connection terminal for internal oscillator
2	VSEN	I	Auxiliary voltage sense terminal. The LED current is controlled based on the detection result with this terminal.
3	VIN	I	PFC and TRIAC dimming operates based on the detection result with this terminal.
4	BLDR	0	Output terminal for control of external bleeder MOSFET.
5	GND	Р	Grand terminal.
6	ISEN	_	Primary current sense terminal. The LED current is controlled based on the detection result with this terminal.
7	GATE	0	Output terminal for control of external power MOSFET.
8	VCC	ΡI	Power supply input terminal.

I: input terminal, O: output terminal, P: power supply and ground

7. Absolute Maximum Ratings ($T_a = 25^{\circ}C$)

Characteristics	Symbol	Rating Note1	Unit
Supply voltage	V _{CC}	-0.3~ 40	V
OREF terminal voltage	VOREF	-0.3~ 6.0	V
VSEN terminal voltage	V _{VSEN}	-0.7~ 6.0	V
VIN terminal voltage	V _{VIN}	-0.3~ 6.0	V
BLDR terminal voltage	VBLDR	-0.3~ V _{CC}	V
ISEN terminal voltage	VISEN	-0.3~ 6.0	V
GATE terminal voltage	VGATE	-0.3~V _{CC}	V
Operating temperature	Topr	-40~85	°C
Storage temperature	T _{stg}	-55~150	°C
Thermal resistance	R _{th(j-a)}	90 Note3	°C/W
Power dissipation	PD	1.38 Note3,4	W

Note1: Voltage is ground referenced.

Note2: PCB condition is 76.2×114.3×1.6mm (JEDEC 4 layer substrate)

Note3: When ambient temperature is 25°C or more. Every time ambient temperature exceeded 1°C, please decrease 1/Rth(j-a).

Ta : the ambient air temperature of IC.

Topr : the ambient air temperature of IC under operation.

: It is the junction temperature of IC under operation.

Tj maximum is restricted by the TSD (thermal shutdown) circuit.

Tj maximum recommends carrying out a thermal design within the limit of a 120 degreeC

Cautions on absolute maximum ratings

The absolute maximum ratings of a semiconductor device are a set of ratings that must not be exceeded, even for a moment. Do not exceed any of these ratings.

Exceeding the rating(s) may cause the device breakdown, damage or deterioration, and may result injury by explosion or combustion. The value of even one parameter of the absolute maximum ratings should not be exceeded under any circumstances. This device does not have over-voltage protection. Therefore, the device is damaged if a voltage exceeding its rated maximum is applied.

All voltage ratings including supply voltages must always be followed. The section on the protection features on the latter page should also be referred to.

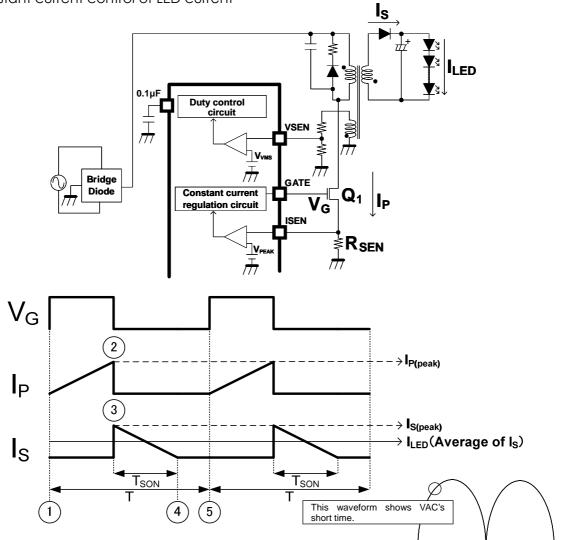
Тj

8. Electrical Characteristics (Unless otherwise noted, $T_a = -40 \sim 85 \circ C$, $V_{CC}=15V$)

Symbol	Test Circuit	Test Conditions	Min	Typ.	Max	Unit
			•			
V _{CC(MAX)}					25	V
linst		VIN = 10 V, CVCC = 10 µF		10	15	μA
lcc		BLDR=OFF,GATE=OFF		1.7	2.5	mA
Vz		T _A = 25°C, I _z = 5 mA	29			V
VUVLO(REL)		V _{CC} rising	11	12	13	V
V _{UVLO(OPE)}		V _{cc} falling	6.5	7.5	8.5	V
			•			
VIN			0		1.8	V
V _{VIN-OVD}			1.85	2.10	2.35	V
Vang_det			0.10	0.14	0.18	V
VBLDR			0.22	0.28	0.34	V
R _{BLDRH}		Igate=-5mA	_	300	_	Ω
Rbldrl		I _{GATE} =+5mA	_	300	_	Ω
VBLDR				Vcc		
I _{IN(Vsen)}		$V_{SENSE} = 2 V$			1	μΑ
Vvms			0.10	0.14	0.18	V
VOOP		T _A = 25°C	1.85	2.10	2.35	V
VOSP			0.10	0.14	0.18	V
Rgateh		Igate=-10mA	_	30	_	Ω
Rgatel		IGATE=+10mA	_	50	_	Ω
trgate		C _L =330pF, 10%to90%,T _A = 25°C	_	50	_	ns
t _{fGATE}		C _L =330pF, 90%to10%,T _A = 25°C	_	30	_	ns
fsw(MAX)			200	_	_	kHz
V _{BLDR}			_	Vcc	_	
VOCP			1.85	2.10	2.35	V
VOCP			1.85	2.10	2.35	V
V _{SROP}			0.10	0.14	0.18	V
T BLANK		Ta=25°C	0.2	0.3	0.4	μS
TOTP		Temperature rising		140		°C
T _{otp(hys)}		Temperature falling		20		°C
	V _{CC(MAX)} IINST I _{CC} V _Z V _{UVL0(REL)} V _{UVL0(OPE)} V _{IN} V _{UN-OVD} V _{ANG_DET} V _{BLDR} R _{BLDRH} R _{BLDRL} V _{BLDR} I _{IN} (vsen) V _{VMS} V _{OOP} V _{OSP} R _{GATEH} R _{GATEL} † _{rGATE} † _{rGATE} † _{rGATE} † _{rGATE} † _{rGATE} † _{rGATE} † _{rGATE} † _{rGATE} T _{OTP}	Symbol Circuit Vcc(mAX) Inst Icc Vz Vz Vuvlo(REL) Vuvlo(PE) Vuvlo(OPE) Vin Vuvlo(PE) Vin Volop Vosp P Rgateh Rgateh Rgate P trgate P fsw(max) Vocp VocP VocP VocP VocP VocP Totp	SymbolCircuitTest Conditions $V_{CC(MAX)}$ InstVIN = 10 V, CVCC = 10 µF Icc $BLDR=OFF, GATE=OFF$ V_2 $T_A = 25^{\circ}C$, $I_2 = 5 mA$ $V_{UVLO(REL)}$ V_{CC} rising $V_{UVLO(OFE)}$ V_{CC} falling V_{UN-OVD} V_{CC} falling V_{IN-OVD} V_{CC} falling V_{BLDR} IGATE=-5mA R_{BLDRH} IGATE=+5mA V_{BLDR} IGATE=+5mA V_{BLDR} VSENSE = 2 V V_{VMS} V_{OOP} $T_A = 25^{\circ}C$ V_{OSP} V_{OOP} $T_A = 25^{\circ}C$ V_{OSP} $I_{IGATE}=+10mA$ R_{GATEL} IGATE=+10mA t_{rGATE} $C_L=330pF, 10\%to90\%, T_A = 25^{\circ}C$ t_{rGATE} $C_L=330pF, 90\%to 10\%, T_A = 25^{\circ}C$ V_{OCP} V_{OCP} V_{OCP} $I_{TG}=25^{\circ}C$ V_{OCP} $T_{G}=25^{\circ}C$ T_{OTP} Temperature rising	Symbol Circuit Test Conditions Min $V_{CC(MAX)}$ VIN = 10 V, CVCC = 10 µF Inst Inst VIN = 10 V, CVCC = 10 µF Icc BLDR=OFF,GATE=OFF V Inst 29 V_{Z} Ta = 25°C, Iz = 5 mA 29 $V_{UVLO(REL}$ V_{CC} rising 11 $V_{UVLO(REL}$ V_{CC} falling 6.5 V_{IN} 0 0 V_{UNLOVD} 1.85 0.10 V_{IN} 0 0.22 R_{BLDR} IGATE=-5mA V_{BLDR} IGATE=-5mA V_{BLDR} IGATE=+5mA V_{BLDR} 0.10 0.10 V_{OOP} Ta = 25°C 1.85 V_{OSP} 0.10 R_{GATEH} IGATE=10mA R_{GATEH} IGATE=10mA R_{GATEH} IGATE=+10mA R_{GATEH} IGATE=+10mA V_{GCP} 1.85	Symbol Circuit Test Conditions Min Typ. V Inst VIN = 10 V, CVCC = 10 µF 10 Icc BLDR=OFF,GATE=OFF 1.7 V Vz TA = 25°C, Iz = 5 mA 29 Vuvio(REL) Vcc rising 11 12 Vuvio(REL) Vcc rising 6.5 7.5 Vin 0 0 0 Vuvio(REL) Vcc falling 6.5 7.5 Vin 0 0 0 0 Vuvio(REL) Vcc falling 0.10 0.14 VBLDR 0.22 0.28 0.10 0.14 VBLDR 0 0 Vcc 0 0 Valor 0 0.10 0.14 0 0 0 VBLDR 0.22 0.28 0.10 0.14 0 0 VBLDR 0.010 0.14 0 0 0 0 0 Voxb 0 0.010 0.14	Symbol Circuit Test Conditions Min Typ. Mdx V _{CC(MAX)} Inst VIN = 10 V, CVCC = 10 µF 10 15 Icc BLDR=OFF,GATE=OFF 1.7 2.5 V _Z TA = 25°C, Iz = 5 mA 29

9. Application Information

9-1Constant current control of LED current



Note: This waveform shows VAC's short time.

- 1: Q_1 is turned on, and I_P flows to the primary-side of transformer.
- 2: IP is detected by ISEN terminal when IP reaches IP(peak), and Q1 is turned off.
 - *I_{P(peak)}= V_{PEAK}/R_{SEN}
- 3: $I_{S(peak)}$ is generated on the secondary-side of transformer. * $I_{S(peak)} = I_{P(peak)} \times Ntr = V_{PEAK}/R_{SEN} \times Ntr$
 - *Ntr: Ratio of transformer winding on the primary-side and the secondary-side.
- 4: This current Is decreases as the energy charged in the transformer decreases. And, it becomes 0mA.
 - When Is becomes 0mA, it is detected by VSEN terminal. As a result, TSON can be detected.
- 5: The frequency control circuit controls T so that TSON/T may become constant.

The LED current can be calculated by the following expressions. IC keeps the LED current constant by controlling V_{PEAK} and T_{SON}/T .

 I_{LED} (Average of Is)= $I_{S(peak)} \times 1/2 \times T_{SON}/T \times 2/\pi$

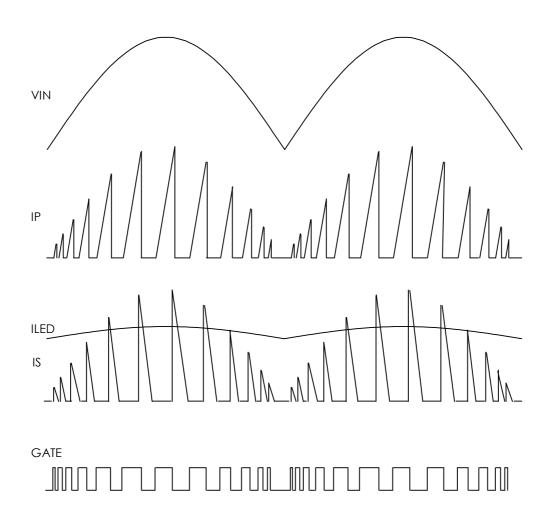
```
= I_{P(peak)} \times Ntr \times 1/2 \times T_{SON}/T \times 2/\pi
```

= $V_{PEAK}/R_{SEN} \times Ntr \times 1/2 \times T_{SON}/T \times 2/\pi$

Application Condition : Tson/T = 4/7 (typ.), 1/T = 100 kHz ($30 kHz \sim 200 kHz$)

9-2 One converter PFC

This IC adjusts V_{PEAK} according to AC shape of wave form detected with the V_{IN} terminal. As a result, I_P near the sine wave is achieved and power factor will near 0.9



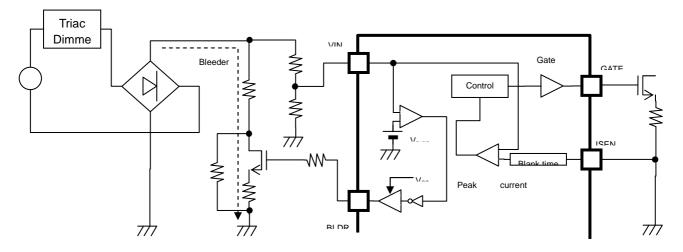
The output capacitance is necessary for LED to become smooth. The On time of GATE waveform changes by the PFC with the upper figure.

Note)

There are image, and anytime's different from the actual wave form.

TOSHIBA

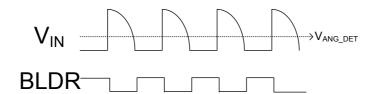
9-3 TRIAC Dimming function



Conduction angle of modulation AC signal of the triac dimmer input to the VIN terminal is detected in threshold $V_{ANG-DET}$. The LED current is changed by adjusting V_{PEAK} by the detection result.

Triac dimming range is 5% to 100%. The input voltage of VIN terminal and BLDR terminal is 0V to 1.8V.

Threshold voltage of Triac conduction angle	Range of VIN		
VAng-DET≦0.14V (TYP)	0~1.8V		



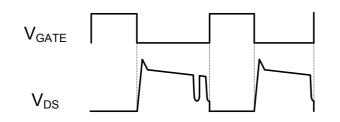
The bleeder current supply terminal changes depending on the input voltage to VIN terminal.

VIN terminal input voltage condition	The breeder current supply terminal		
Less than 0.28V	BLDR ON		
Over than 0.28V	BLDR Off		

9-4 Valley switch operation

The EMI noise and the switching loss are decreased by doing the switching when V_{DS} of MOS is the lowest. This IC detects the minimum of V_{DS} by VSEN terminal.

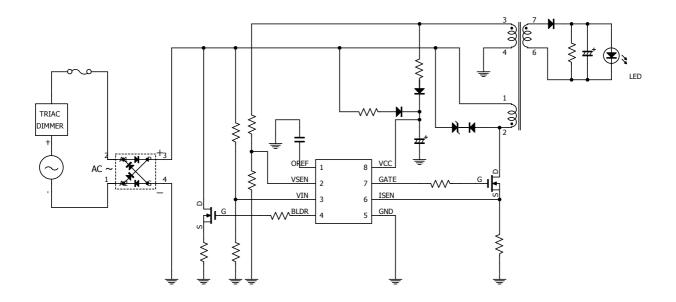
When it doesn't meet the condition of turning on by T_{SON}/T control, the valley might be skipped.



10. Detection function

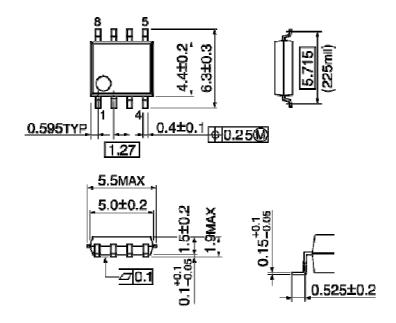
Detection function	Effect	Detection point	detection level	Operation at the time of detection	Release condition	
Over temperature detection (OTD)	Over heating prevention	Internal temperature of IC	140°C(TYP)		Temperature falls by 20°C(TYP) or more from a detection level	
Under voltage lockout (UVLO)	Malfunction prevention by IC Supply voltage abnormality	VCC terminal voltage	7.5V(TYP)	GATE terminal output voltage is set to 0V, and	Voltage rises by 4.5V(TYP) or more From a detection level	
VIN over voltage detection (VIN-OVD)	Malfunction prevention by IC Supply voltage abnormality	VIN terminal voltage	2.10V(TYP) for 15 continuous half AC cycles	switching	Voltage falls by blow detection level	
Output open circuit detection (OOD)	Over-voltage prevention by LED open-circuit of LED	VSEN terminal voltage	2.10V(TYP) for 2 continuous switching cycles			
Output short circuit Detection (OSD)	Malfunction prevention by IC by Short-circuit of LED	VSEN terminal voltage	0.14V(TYP)	Repetition of Starting and Stop.		
Over current Detection (OCD)	Over current prevention by circuit short-circuit	ISEN terminal voltage	2.10V(TYP)	GATE terminal output voltage is set to 0V, and	The function of UVLO	
ISEN line open detection (IOD)	Open line of ISEN to Rsense	ISEN terminal voltage	2.10V(TYP)	switching control of Power MOS is stopped.		

11. Application figure



10. Package dimension

Unit : mm



Weight: 0.07 g (Typ.)

Notes on Contents

1. Block Diagrams

Some of the functional blocks, circuits, or constants in the block diagram may be omitted or simplified for explanatory purposes.

2. Equivalent Circuits

The equivalent circuit diagrams may be simplified or some parts of them may be omitted for explanatory purposes.

3. Timing Charts

Timing charts may be simplified for explanatory purposes.

4. Application Circuits

The application circuits shown in this document are provided for reference purposes only. Thorough evaluation is required, especially at the mass production design stage.

Toshiba does not grant any license to any industrial property rights by providing these examples of application circuits.

5. Test Circuits

Components in the test circuits are used only to obtain and confirm the device characteristics. These components and circuits are not guaranteed to prevent malfunction or failure from occurring in the application equipment.

IC Usage Considerations

Notes on handling of ICs

[1] The absolute maximum ratings of a semiconductor device are a set of ratings that must not be exceeded, even for a moment. Do not exceed any of these ratings.

Exceeding the rating(s) may cause the device breakdown, damage or deterioration, and may result injury by explosion or combustion.

- [2] Use an appropriate power supply fuse to ensure that a large current does not continuously flow in case of over current and/or IC failure. The IC will fully break down when used under conditions that exceed its absolute maximum ratings, when the wiring is routed improperly or when an abnormal pulse noise occurs from the wiring or load, causing a large current to continuously flow and the breakdown can lead smoke or ignition. To minimize the effects of the flow of a large current in case of breakdown, appropriate settings, such as fuse capacity, fusing time and insertion circuit location, are required.
- [3] If your design includes an inductive load such as a motor coil, incorporate a detection circuit into the design to prevent device malfunction or breakdown caused by the current resulting from the inrush current at power ON or the negative current resulting from the back electromotive force at power OFF. IC breakdown may cause injury, smoke or ignition. Use a stable power supply with ICs with built-in detection functions. If the power supply is unstable, the detection function may not operate, causing IC breakdown. IC breakdown may cause injury, smoke or ignition.
- [4] Do not insert devices in the wrong orientation or incorrectly.

Make sure that the positive and negative terminals of power supplies are connected properly. Otherwise, the current or power consumption may exceed the absolute maximum rating, and exceeding the rating(s) may cause the device breakdown, damage or deterioration, and may result injury by explosion or combustion.

In addition, do not use any device that is applied the current with inserting in the wrong orientation or incorrectly even just one time.

[5] Carefully select external components (such as inputs and negative feedback capacitors) and load components (such as speakers), for example, power amp and regulator.

If there is a large amount of leakage current such as input or negative feedback condenser, the IC output DC voltage will increase. If this output voltage is connected to a speaker with low input withstand voltage, overcurrent or IC failure can cause smoke or ignition. (The over current can cause smoke or ignition from the IC itself.) In particular, please pay attention when using a Bridge Tied Load (BTL) connection type IC that inputs output DC voltage to a speaker directly.

RESTRICTIONS ON PRODUCT USE

- Toshiba Corporation, and its subsidiaries and affiliates (collectively "TOSHIBA"), reserve the right to make changes to the information in this document, and related hardware, software and systems (collectively "Product") without notice.
- This document and any information herein may not be reproduced without prior written permission from TOSHIBA. Even with TOSHIBA's written permission, reproduction is permissible only if reproduction is without alteration/omission.
- Though TOSHIBA works continually to improve Product's quality and reliability, Product can malfunction or fail. Customers are responsible for complying with safety standards and for providing adequate designs and safeguards for their hardware, software and systems which minimize risk and avoid situations in which a malfunction or failure of Product could cause loss of human life, bodily injury or damage to property, including data loss or corruption. Before customers use the Product, create designs including the Product, or incorporate the Product into their own applications, customers must also refer to and comply with (a) the latest versions of all relevant TOSHIBA information, including without limitation, this document, the specifications, the data sheets and application notes for Product and the precautions and conditions set forth in the "TOSHIBA Semiconductor Reliability Handbook" and (b) the instructions for the applications, including but not limited to (a) determining the appropriateness of the use of this Product in such design or applications; (b) evaluating and determining the applicability of any information contained in this document, or in charts, diagrams, programs, algorithms, sample application circuits, or any other referenced documents; and (c) validating all operating parameters for such designs and applications.
- PRODUCT IS NEITHER INTENDED NOR WARRANTED FOR USE IN EQUIPMENTS OR SYSTEMS THAT REQUIRE EXTRAORDINARILY HIGH LEVELS OF QUALITY AND/OR RELIABILITY, AND/OR A MALFUNCTION OR FAILURE OF WHICH MAY CAUSE LOSS OF HUMAN LIFE, BODILY INJURY, SERIOUS PROPERTY DAMAGE AND/OR SERIOUS PUBLIC IMPACT ("UNINTENDED USE"). Except for specific applications as expressly stated in this document, Unintended Use includes, without limitation, equipment used in nuclear facilities, equipment used in the aerospace industry, medical equipment, equipment used for automobiles, trains, ships and other transportation, traffic signaling equipment, equipment used to control combustions or explosions, safety devices, elevators and escalators, devices related to electric power, and equipment used in finance-related fields. IF YOU USE PRODUCT FOR UNINTENDED USE, TOSHIBA ASSUMES NO LIABILITY FOR PRODUCT. For details, please contact your TOSHIBA sales representative.
- Do not disassemble, analyze, reverse-engineer, alter, modify, translate or copy Product, whether in whole or in part.
- Product shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable laws or regulations.
- The information contained herein is presented only as guidance for Product use. No responsibility is assumed by TOSHIBA for any infringement of patents or any other intellectual property rights of third parties that may result from the use of Product. No license to any intellectual property right is granted by this document, whether express or implied, by estoppel or otherwise.
- ABSENT A WRITTEN SIGNED AGREEMENT, EXCEPT AS PROVIDED IN THE RELEVANT TERMS AND CONDITIONS OF SALE FOR PRODUCT, AND TO THE MAXIMUM EXTENT ALLOWABLE BY LAW, TOSHIBA (1) ASSUMES NO LIABILITY WHATSOEVER, INCLUDING WITHOUT LIMITATION, INDIRECT, CONSEQUENTIAL, SPECIAL, OR INCIDENTAL DAMAGES OR LOSS, INCLUDING WITHOUT LIMITATION, LOSS OF PROFITS, LOSS OF OPPORTUNITIES, BUSINESS INTERRUPTION AND LOSS OF DATA, AND (2) DISCLAIMS ANY AND ALL EXPRESS OR IMPLIED WARRANTIES AND CONDITIONS RELATED TO SALE, USE OF PRODUCT, OR INFORMATION, INCLUDING WARRANTIES OR CONDITIONS OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, ACCURACY OF INFORMATION, OR NONINFRINGEMENT.
- Do not use or otherwise make available Product or related software or technology for any military purposes, including without limitation, for the design, development, use, stockpiling or manufacturing of nuclear, chemical, or biological weapons or missile technology products (mass destruction weapons). Product and related software and technology may be controlled under the applicable export laws and regulations including, without limitation, the Japanese Foreign Exchange and Foreign Trade Law and the U.S. Export Administration Regulations. Export and re-export of Product or related software or technology are strictly prohibited except in compliance with all applicable export laws and regulations.
- Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. Please use Product in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. TOSHIBA ASSUMES NO LIABILITY FOR DAMAGES OR LOSSES OCCURRING AS A RESULT OF NONCOMPLIANCE WITH APPLICABLE LAWS AND REGULATIONS.





Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001 Адрес: 105318, г.Москва, ул.Щербаковская д.З, офис 1107

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж: moschip.ru moschip.ru_4

moschip.ru_6 moschip.ru_9